1. General description

NPN high power bipolar transistor in a power DPAK, TO-252 (SOT428C) Surface-Mounted Device (SMD) plastic package.

PNP complement: MJD42C-Q

2. Features and benefits

- · High thermal power dissipation capability
- · High energy efficiency due to less heat generation
- · Electrically similar to popular MJD41 series
- · Low collector emitter saturation voltage
- Fast switching speeds
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Power management
- Load switch
- · Linear mode voltage regulator
- · Constant current drive backlighting application
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	100	V
V _{EBO}	emitter-base voltage	open collector	-	-	6	V
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	10	Α
h _{FE}	DC current gain	V_{CE} = 4 V; I_{C} = 0.3 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	30	-	-	
		V_{CE} = 4 V; I_{C} = 3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	15	-	-	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	
2	С	collector		E
3	Е	emitter		в -[**
mb	С	mounting base; connected to collector	DPAK (SOT428C)	C; mb aaa-029889

6. Ordering information

Table 3. Ordering information

- table of ortaling information						
Type number	Package					
	Name	Description	Version			
MJD41C-Q		Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428C			

7. Marking

Table 4. Marking codes

Type number	Marking code
MJD41C-Q	MJD41CA

8. Limiting values

Table 5. Limiting values

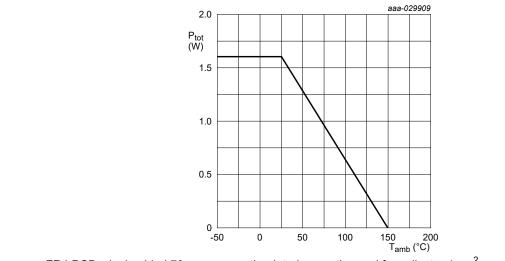
In accordance with the Absolute Maximum Rating System (IEC601134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
Ic	collector current			-	6	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	10	Α
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C	[1]	-	15	W
		T _{amb} ≤ 25 °C	[2]	-	1.6	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Total power dissipation junction to mounting base.

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided 70 μm copper, tin-plated mounting pad for collector 1 cm².

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FR4 PCB, single-sided 70 µm copper, tin-plated, mounting pad for collector 1 cm².

Fig. 1. Power derating curves SOT428C

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	79	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	9	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided 70 µm copper, tin-plated mounting pad for collector 1 cm².

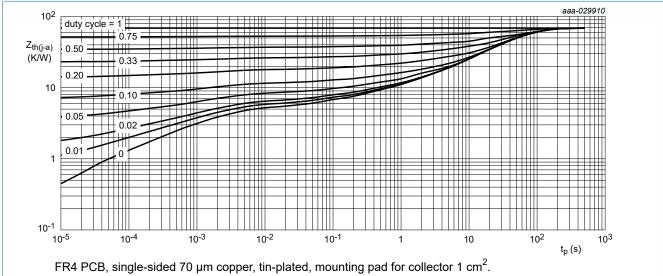


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	1	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	1	μΑ
h _{FE}	DC current gain	V_{CE} = 4 V; I_{C} = 0.3 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	30	-	-	
		V_{CE} = 4 V; I_{C} = 3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	15	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 6 A; I_B = 600 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.5	V
V_{BE}	base-emitter voltage	V_{CE} = 4 V; I_{C} = 6 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	2	V
h _{fe}	small-signal current gain	V_{CE} = 10 V; I_{C} = 500 mA; f = 1 kHz; pulsed; $t_{p} \le 300$ µs; $\delta \le 0.02$; T_{amb} = 25 °C	20	-	-	
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 500 mA; f = 100 MHz; T_{amb} = 25 °C	3	-	-	MHz

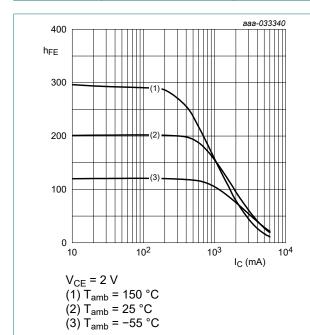


Fig. 3. DC current gain as a function of collector current; typical values

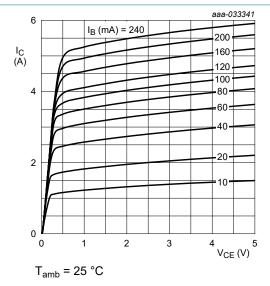


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

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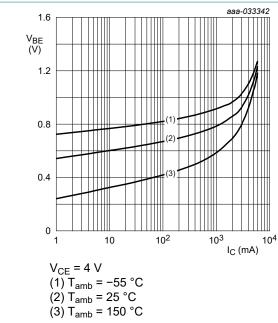
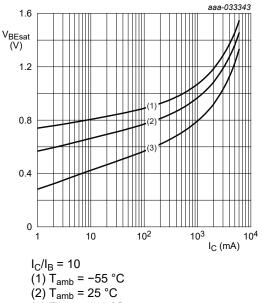
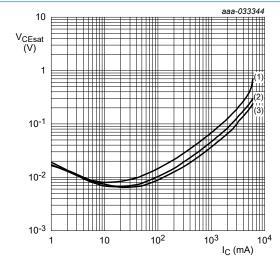


Fig. 5. Base-emitter voltage as a function of collector current; typical values



(3) $T_{amb} = 150 \, ^{\circ}C$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



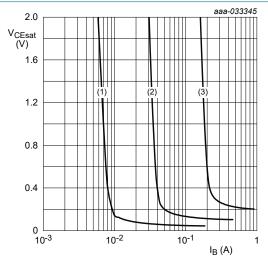
 $I_{\rm C}/I_{\rm B} = 10$

(1) T_{amb} = 150 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



T_{amb} = 25 °C

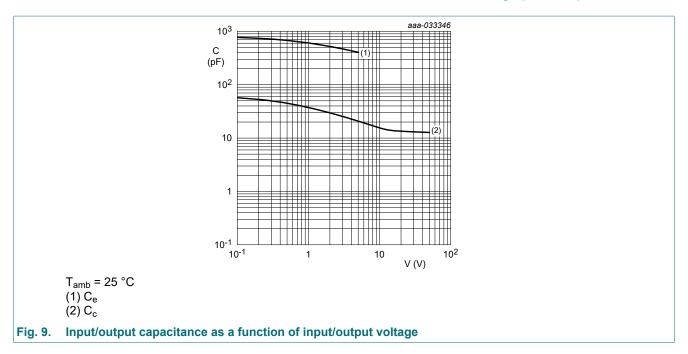
 $(1) I_C = 1 A$

 $(2) I_C = 2.5 A$

(3) $I_C = 5 A$

Fig. 8. Collector-emitter saturation region as a function of base current; typical values

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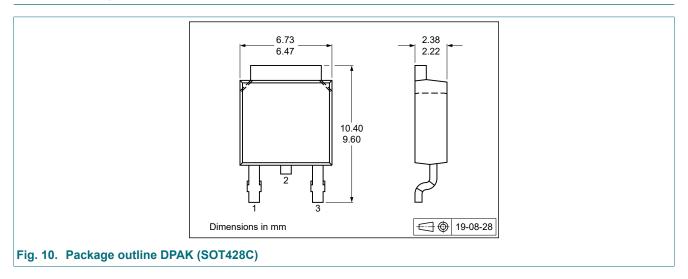


11. Test information

Quality information

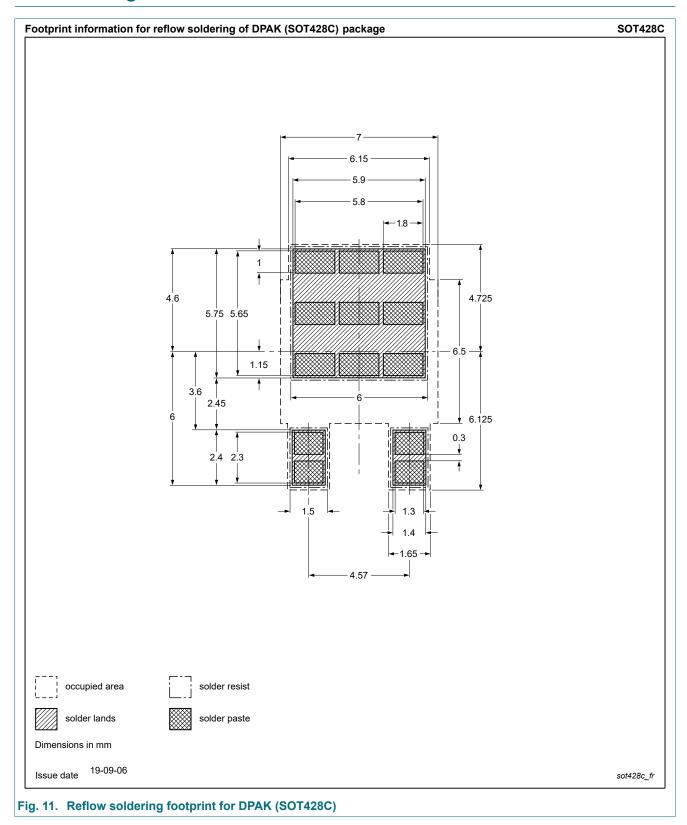
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
MJD41C-Q v.1	20210517	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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MJD41C-Q

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